N-Channel 150-V (D-S) MOSFET

Key Features:

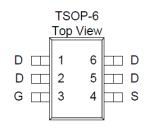
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

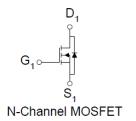
| Typical | App | lication | ıs: |
|----------------|-----|----------|-----|
| - 7 | | | |

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY | | | |
|---------------------|-------------------------------|-----|--|
| V _{DS} (V) | I _D (A) | | |
| 150 | 700 @ V _{GS} = 10V | 1.2 | |
| | 1200 @ V _{GS} = 4.5V | 1 | |







| ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED) | | | | | | |
|---|----|--------|----------------|------------|-------|--|
| Parameter | | | Symbol | Limit | Units | |
| Drain-Source Voltage | | | V_{DS} | 150 | V | |
| Gate-Source Voltage | | | | ±20 | V | |
| Continuous Dunin Compant 8 | | (=25°C | ı | 1.2 | А | |
| Continuous Drain Current ^a | T | _=70°C | I _D | 1 | | |
| Pulsed Drain Current ^b | | | | 10 | | |
| Continuous Source Current (Diode Conduction) a | Is | 2.5 | Α | | | |
| Deutan Dissination 8 | | _=25°C | P_{D} | 2 | · W | |
| Power Dissipation ^a | TA | _=70°C | гD | 1.3 | | |
| Operating Junction and Storage Temperature Range | | | T_J, T_{sta} | -55 to 150 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-----------------|-------|------|--|--|
| Parameter | Symbol | Maximum | Units | | | |
| Maximum Junction-to-Ambient ^a | t <= 10 sec | $R_{\theta JA}$ | 62.5 | °C/W | | |
| Maximum Junction-to-Ambient | Steady State | IXOJA | 110 | C/VV | | |

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit | |
|---------------------------------|---------------------|--|-----|------|------|-------|--|
| Static | | | | | | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$ | 1 | | | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ±100 | nA | |
| Zero Gate Voltage Drain Current | | $V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 | l uA | |
| Zero Gate Voltage Brain Garrent | I _{DSS} | $V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | | | 10 | uA | |
| On-State Drain Current | I _{D(on)} | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 10 | | | Α | |
| Drain-Source On-Resistance | r | $V_{GS} = 10 \text{ V}, I_D = 1.2 \text{ A}$ | | | 700 | mΩ | |
| Drain-Source On-Resistance | r _{DS(on)} | $V_{GS} = 4.5 \text{ V}, I_D = 1 \text{ A}$ | | | 1200 | 11122 | |
| Forward Transconductance | g _{fs} | $V_{DS} = 15 \text{ V}, I_{D} = 1.2 \text{ A}$ | | 11 | | S | |
| Diode Forward Voltage | V_{SD} | $I_S = 1.3 \text{ A}, V_{GS} = 0 \text{ V}$ | | 0.8 | | V | |
| | | Dynamic | | | | | |
| Total Gate Charge | Q_g | | | 3.5 | | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = 75 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 1 \text{ A}$ | | 1.3 | | nC | |
| Gate-Drain Charge | Q_{gd} | | | 1.5 | | | |
| Turn-On Delay Time | t _{d(on)} | | | 4.4 | | | |
| Rise Time | t _r | $V_{DD} = 75 \text{ V}, R_L = 75 \Omega, I_D = 1 \text{ A},$ | | 4.9 | | ns | |
| Turn-Off Delay Time | $t_{d(off)}$ | $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$ | | 18.4 | | 113 | |
| Fall Time | t _f | | | 4.9 | | | |
| Input Capacitance | C _{iss} | | | 356 | | | |
| Output Capacitance | C _{oss} | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 38 | | pF | |
| Reverse Transfer Capacitance | C_{rss} | | | 17 | | | |

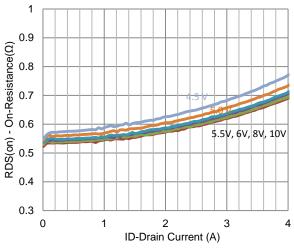
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

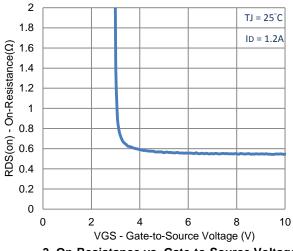
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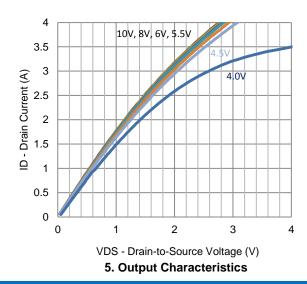
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current

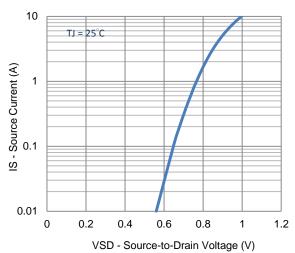


3. On-Resistance vs. Gate-to-Source Voltage

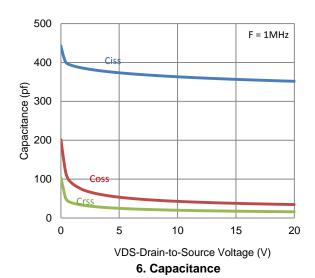


 $TJ = 25^{\circ}C$ ID - Drain Current (A) 1 0 0 1 2 3 4 5

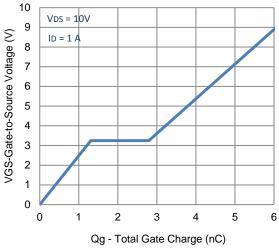
VGS - Gate-to-Source Voltage (V) 2. Transfer Characteristics

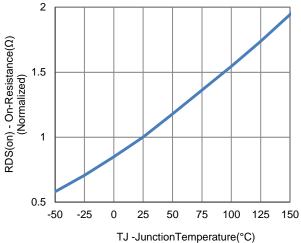


4. Drain-to-Source Forward Voltage



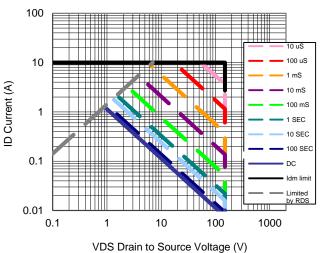
Typical Electrical Characteristics

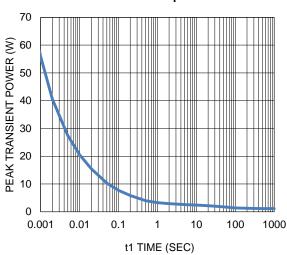




7. Gate Charge

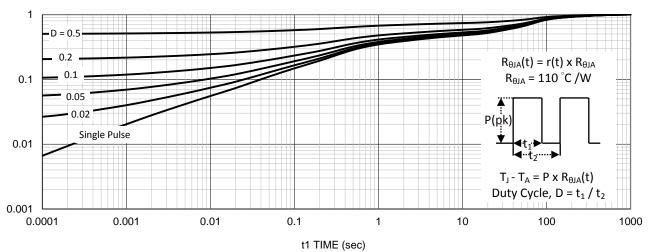






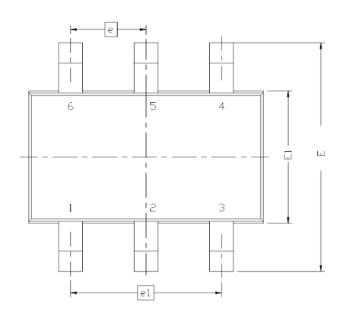
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation

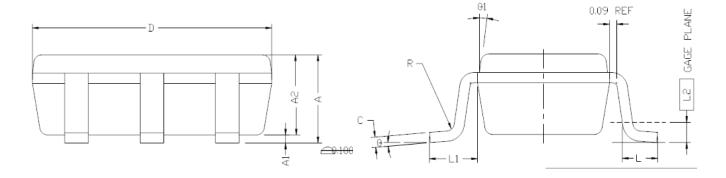


11. Normalized Thermal Transient Junction to Ambient

Package Information



| DIM. | MILLIMETERS | | | | | |
|------|-------------|------|------|--|--|--|
| DIM. | MIN | NDM | MAX | | | |
| Α | 0.935 | | 1.10 | | | |
| A1 | 0.01 | | 0.10 | | | |
| A2 | 0.70 | | 1.00 | | | |
| b | 0.25 | 0.32 | 0.40 | | | |
| C | 0.10 | 0.15 | 0.20 | | | |
| D | 2.95 | 3.10 | | | | |
| Ε | 2.70 | 2.98 | | | | |
| E1 | 1.55 | 1.65 | 1.70 | | | |
| 6 | 0.95 BSC | | | | | |
| L | 0.30 | 0.60 | | | | |
| L1 | 0.60REF | | | | | |
| L2 | 0.25BSC | | | | | |
| R | 0.10 | | | | | |
| θ | 0? | 4? | 8? | | | |
| θ1 | 7? N□M | | | | | |



Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess
 Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The
 Foot.